



STC08DE150HP

Hybrid emitter switched bipolar transistor
ESBT® 1500V - 8A - 0.075 Ω

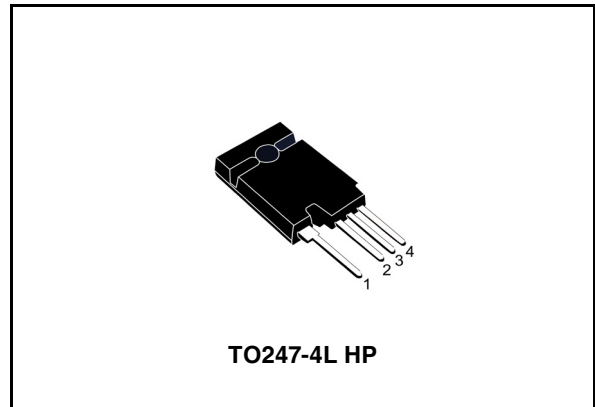
Preliminary Data

General features

Table 1. General features

$V_{CS(ON)}$	I_C	$R_{CS(ON)}$
0.6V	8A	0.075 Ω

- Low equivalent on resistance
- Very fast-switch, up to 150 kHz
- Squared RBSOA, up to 1500 V
- Very low C_{ISS} driven by $R_G = 47 \Omega$
- In compliance with the 2002/93/EC European Directive



Description

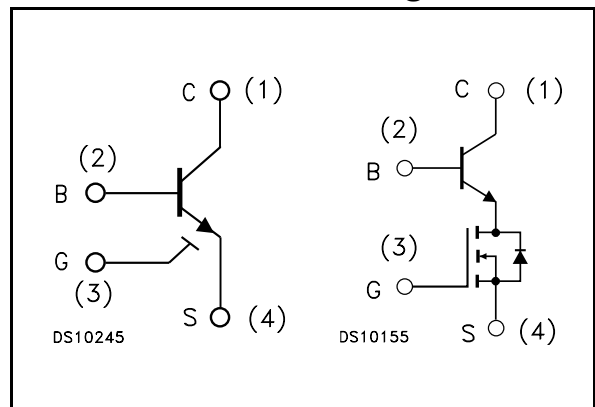
The STC08DE150HP is manufactured in a hybrid structure, using dedicated high voltage Bipolar and low voltage MOSFET technologies, aimed at providing the best performance in ESBT topology.

The STC08DE150HP is designed for use in aux flyback smps for any three phase application.

Applications

- Single switch SMPS based on three phase mains

Internal schematic diagrams



Order codes

Part Number	Marking	Package	Packing
STC08DE150HP	C08DE150HP	TO247-4L HP	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{CS(SS)}$	Collector-source voltage ($V_{BS}=V_{GS}=0V$)	1500	V
$V_{BS(OS)}$	Base-source voltage ($I_C=0$, $V_{GS}=0V$)	30	V
$V_{SB(OS)}$	Source-base voltage ($I_C=0$, $V_{GS}=0V$)	9	V
V_{GS}	Gate-source voltage	± 20	V
I_C	Collector current	8	A
I_{CM}	Collector peak current ($t_P < 5ms$)	15	A
I_B	Base current	4	A
I_{BM}	Base peak current ($t_P < 1ms$)	8	A
P_{tot}	Total dissipation at $T_C \leq 25^\circ C$	42	W
T_{stg}	Storage temperature	-40 to 150	$^\circ C$
T_J	Max. operating junction temperature	125	$^\circ C$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.4	$^\circ C/W$

2 Electrical characteristics

($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{\text{CS(SS)}}$	Collector-source current ($V_{\text{BS}} = V_{\text{GS}} = 0\text{V}$)	$V_{\text{CS(SS)}} = 1500\text{V}$			100	μA
$I_{\text{BS(OS)}}$	Base-source current ($I_{\text{C}} = 0, V_{\text{GS}} = 0\text{V}$)	$V_{\text{BS(OS)}} = 30\text{V}$			10	μA
$I_{\text{SB(OS)}}$	Source-base current ($I_{\text{C}} = 0, V_{\text{GS}} = 0\text{V}$)	$V_{\text{SB(OS)}} = 9\text{V}$			100	μA
$I_{\text{GS(OS)}}$	Gate-source leakage ($V_{\text{BS}} = 0\text{V}$)	$V_{\text{GS}} = \pm 20\text{V}$			500	nA
$V_{\text{CS(ON)}}$	Collector-source ON voltage	$V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 8\text{A}$ $I_{\text{B}} = 1.6\text{A}$ $V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 5\text{A}$ $I_{\text{B}} = 0.5\text{A}$		0.6 0.6	1.4	V V
h_{FE}	DC current gain	$I_{\text{C}} = 8\text{A}$ $V_{\text{CS}} = 1\text{V}$ $V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 5\text{A}$ $V_{\text{CS}} = 1\text{V}$ $V_{\text{GS}} = 10\text{V}$	4.5 8	7.5 10		
$V_{\text{BS(ON)}}$	Base-source ON voltage	$V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 8\text{A}$ $I_{\text{B}} = 1.6\text{A}$ $V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 5\text{A}$ $I_{\text{B}} = 0.5\text{A}$		1.5 1	2	V V
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{BS}} = V_{\text{GS}}$ $I_{\text{B}} = 250\mu\text{A}$	1.5	2.2	3	V
C_{iss}	Input capacitance	$V_{\text{CS}} = 25\text{V}$ $f = 1\text{MHz}$ $V_{\text{GS}} = V_{\text{CB}} = 0\text{V}$		750		pF
$Q_{\text{GS(tot)}}$	Gate-source Charge	$V_{\text{GS}} = 10\text{V}$ $I_{\text{C}} = 8\text{A}$ $V_{\text{CS}} = 25\text{V}$ $V_{\text{CB}} = 0\text{V}$		12.5		nC
t_{s} t_{f}	INDUCTIVE LOAD Storage time Fall time	$V_{\text{GS}} = 10\text{V}$ $R_{\text{G}} = 47\Omega$ $V_{\text{Clamp}} = 1200\text{V}$ $t_{\text{p}} = 4\mu\text{s}$ $I_{\text{C}} = 5\text{A}$ $I_{\text{B}} = 0.5\text{A}$		526 8.5		ns ns
t_{s} t_{f}	INDUCTIVE LOAD Storage time Fall time	$V_{\text{GS}} = 10\text{V}$ $R_{\text{G}} = 47\Omega$ $V_{\text{Clamp}} = 1200\text{V}$ $t_{\text{p}} = 4\mu\text{s}$ $I_{\text{C}} = 5\text{A}$ $I_{\text{B}} = 1\text{A}$		884 16		ns ns
V_{CSW}	Maximum collector-source voltage switched without snubber	$R_{\text{G}} = 47\Omega$ $h_{\text{FE}} = 5$ $I_{\text{C}} = 8\text{A}$	1500			V

Table 4. Electrical characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CS(dyn)}$	Collector-source dynamic voltage (500ns)	$V_{CC}=V_{Clamp}=300V$ $V_{GS}=10V$ $I_C=4A$ $I_B=0.8A$ $t_{peak}=500ns$ $R_G=47\Omega$ $I_{Bpeak}=8A (2I_C)$		6		V
$V_{CS(dyn)}$	Collector-source dynamic voltage (1μs)	$V_{CC}=V_{Clamp}=300V$ $V_{GS}=10V$ $I_C=4A$ $I_B=0.8A$ $t_{peak}=500ns$ $R_G=47\Omega$ $I_{Bpeak}=8A (2I_C)$		2.2		V

Note (1) Pulsed duration = 300 μs, duty cycle ≤1.5%

2.1 Electrical characteristics (curves)

Figure 1. Output characteristics

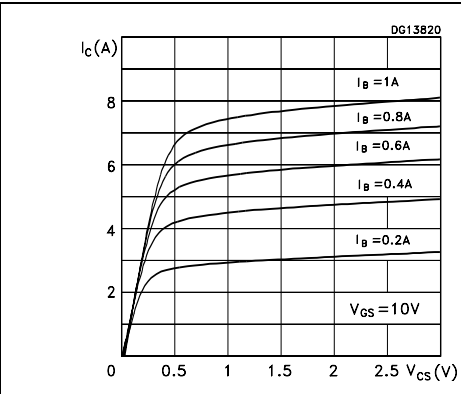


Figure 2. Dynamic collector-emitter saturation voltage

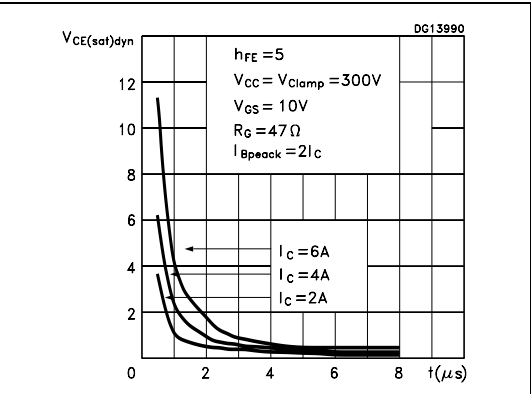


Figure 3. DC current gain

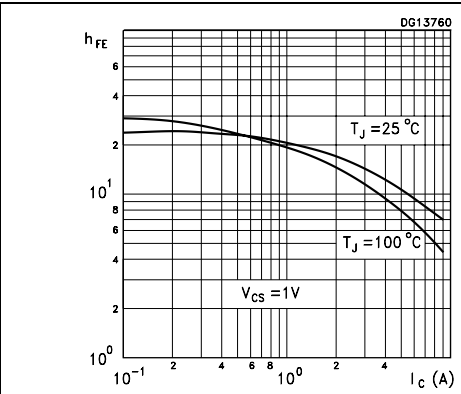


Figure 4. Gate threshold voltage vs temperature

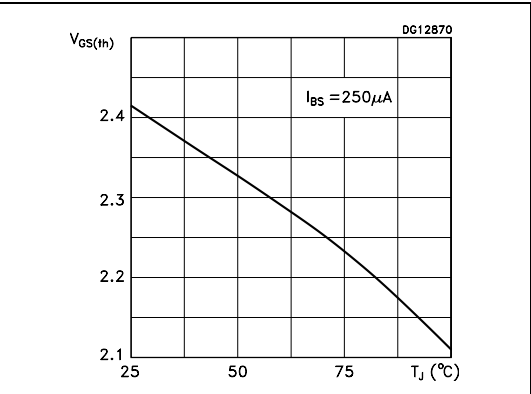


Figure 5. Collector-source On voltage Figure 6. Collector-source On voltage

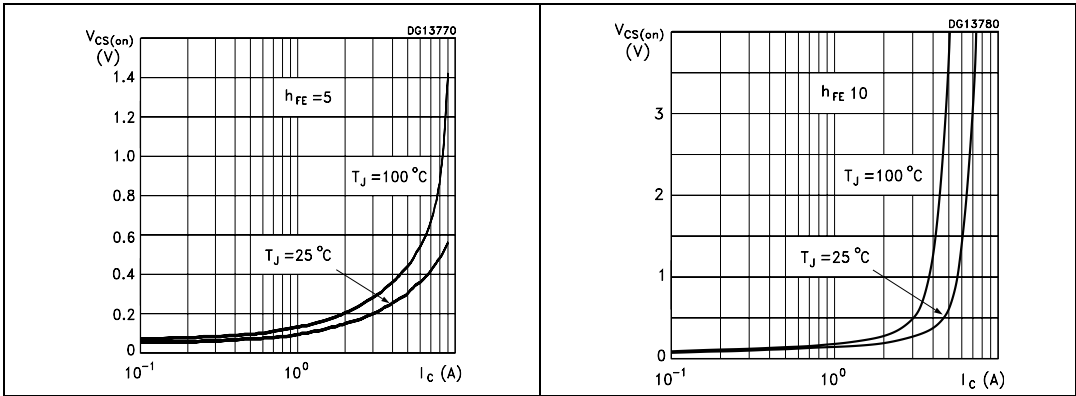


Figure 7. Base-source On voltage Figure 8. Base-source On voltage

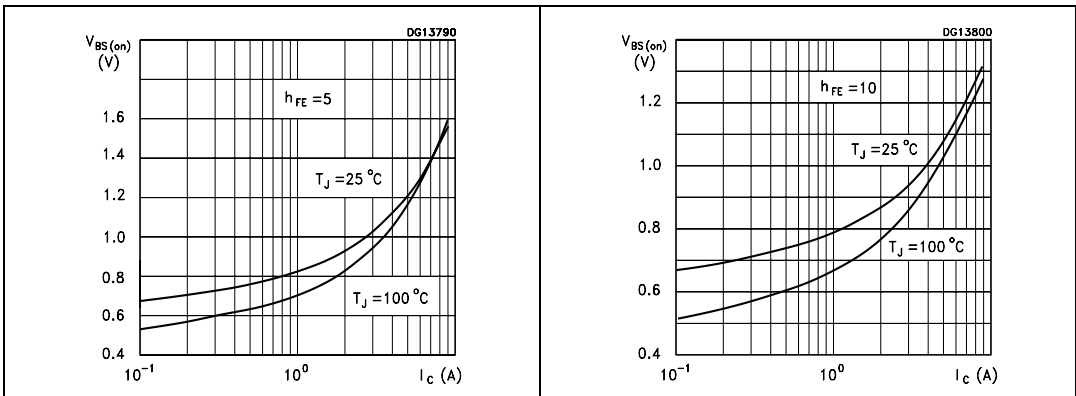
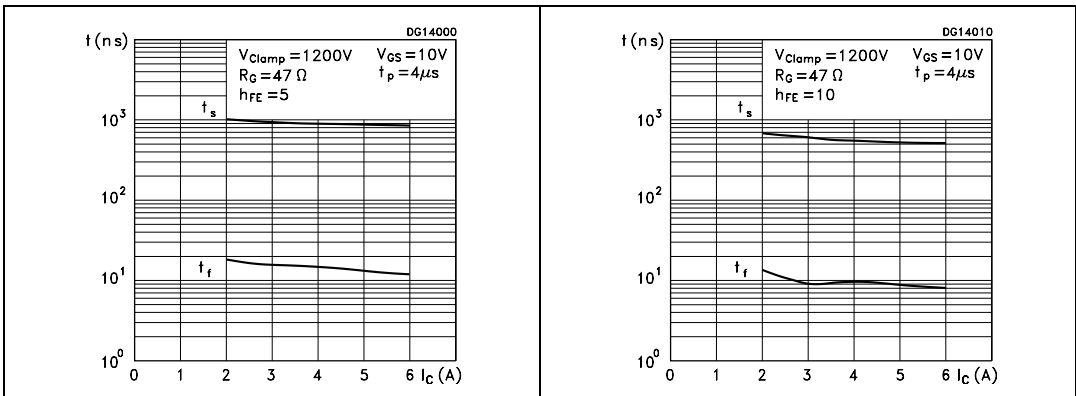
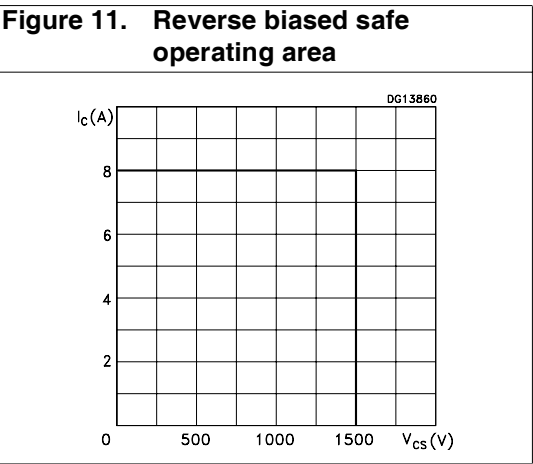


Figure 9. Inductive load switching time Figure 10. Inductive load switching time





2.2 Test circuits

Figure 12. Enlargement FBSOA circuit

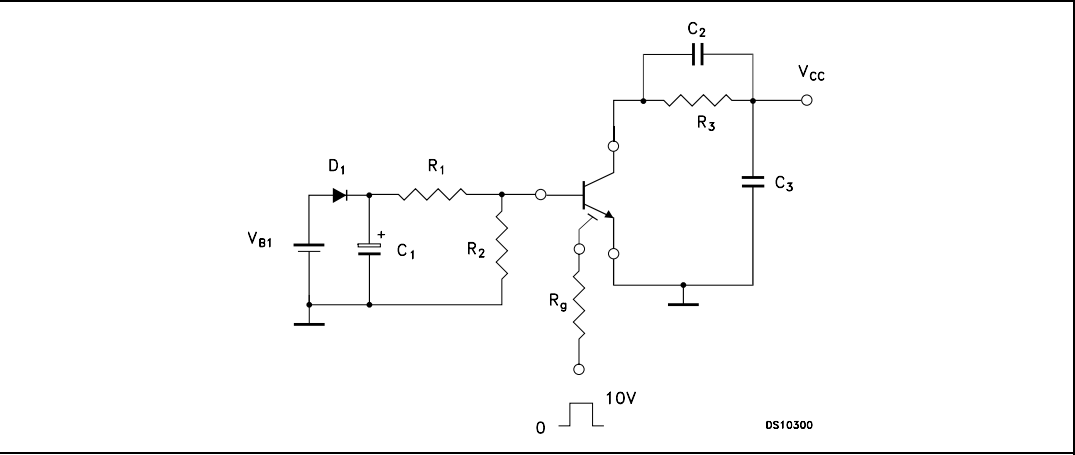


Table 5. Components, values

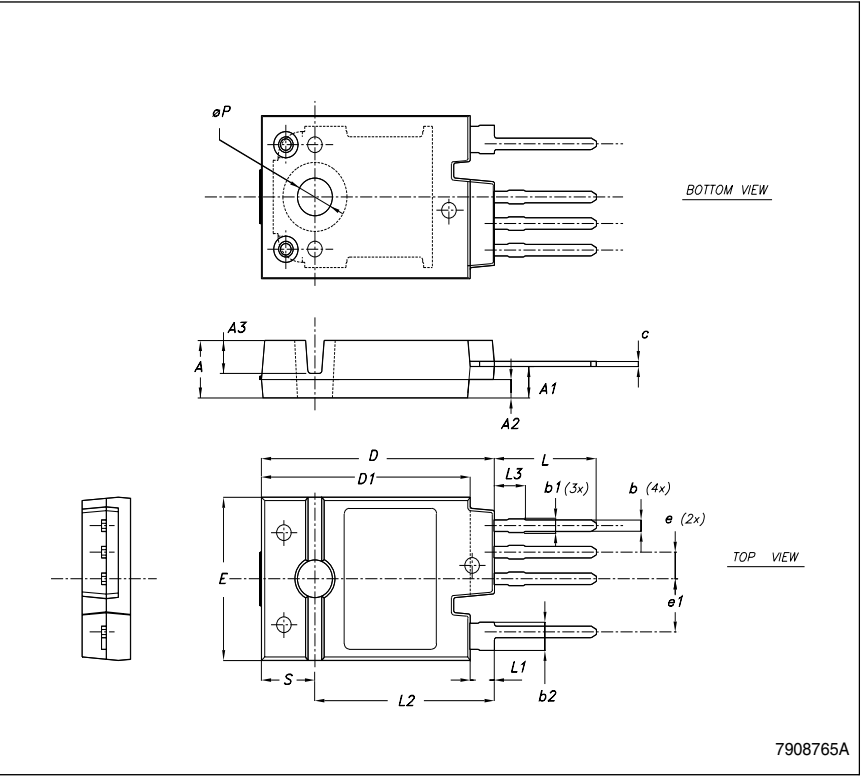
$V_{B1} = 4.16V$	$C_1 = 4700\mu F$
$D_1 = BA157$	$C_2 \leq 1000pF$
$R_1 = 1\Omega$	$V_{CC} = 1500V$
$R_2 = 100\Omega$	$V_g = 10V$
$R_3 = 180\Omega$	Pulse time = $5\mu s$
$R_g = 47\Omega$	

3 **Package mechanical data**

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO247-4LHP MECHANICAL DATA

DIM.	mm.		
	MIN.	TYP	MAX.
A	5.50	5.65	5.80
A1	2.85	3.15	3.25
A2		1.92	
A3		3.18	
b	0.95	1.10	1.30
b1	1.10		1.50
b2	2.50		2.90
c	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
e	2.54		
e1		5.08	
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
øP	3.55		3.65
S		5.50	



4 Revision history

Table 6. Revision history

Date	Revision	Changes
26-Oct-2006	1	First release.

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